

Evaluation of the Virtual Crystal Approximation for Predicting Thermal Conductivity

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Slides

- Macro-theory: $k = \rho C_p \lambda$

- Carrier theory (classical harmonic limit):

$k_{\{x\}} = (kb/V) \sum D_{\{x\}}$: most general (phonons, diffusons, locons, propagons)

$k_{\{x\}} = (kb/V) \sum v_{\{g,x\}}^2 \tau$: phonons

$k_{\{x\}} = (kb/V) \sum v_{\{g,x\}} \Lambda$: phonons ($\Lambda = |v_g| \tau$)

- Λ in SW alloys, compare to a , compare to $k(\Lambda)$.

- Λ in LJ alloys, compare to a , $k(\Lambda)$.

- LJ alloys $k(\omega)$, fast convergence ($k(N_0)$)

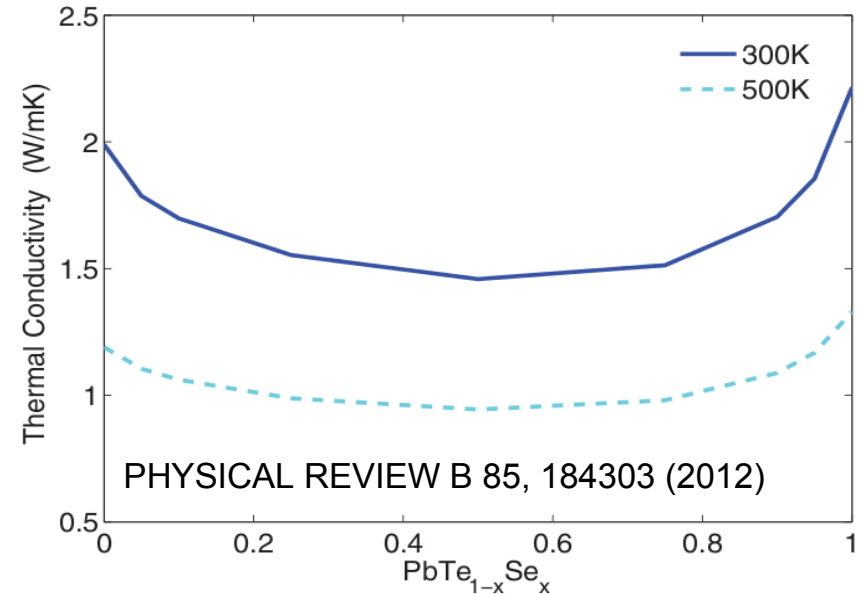
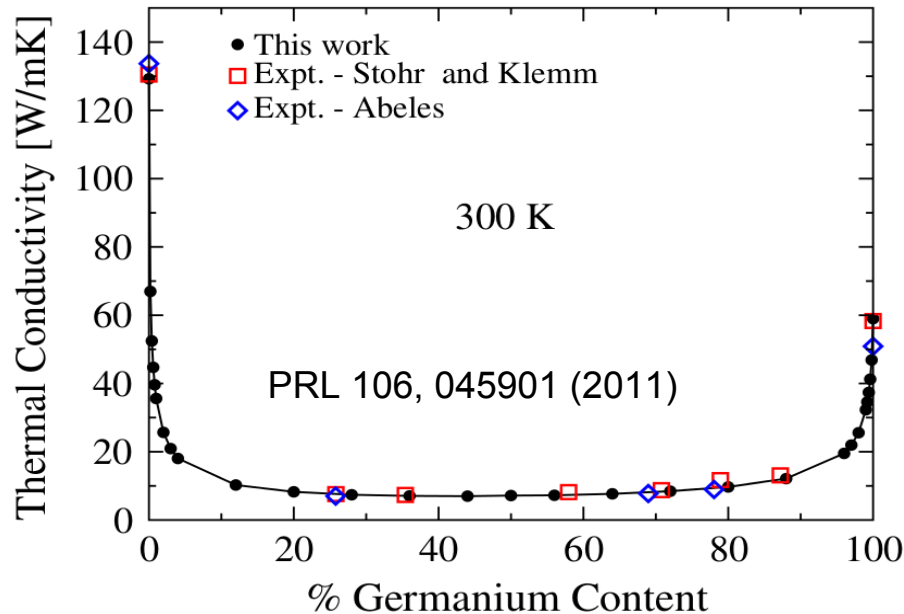
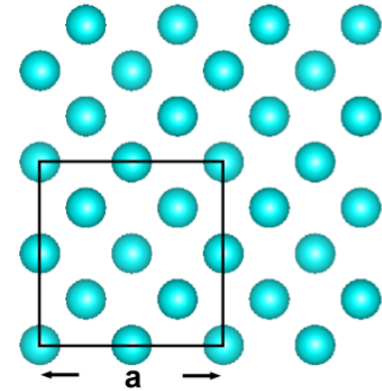
- LJ amorphous, all important modes in a sample $4x$ (2 nm!), no contributions from phonons

- implications for disordered systems, how to beat high scatter limit

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Motivation: DFT predictions

- Computationally expensive DFT, calculations based on unit cell
- Alloys: isotopic effects, thermoelectric materials

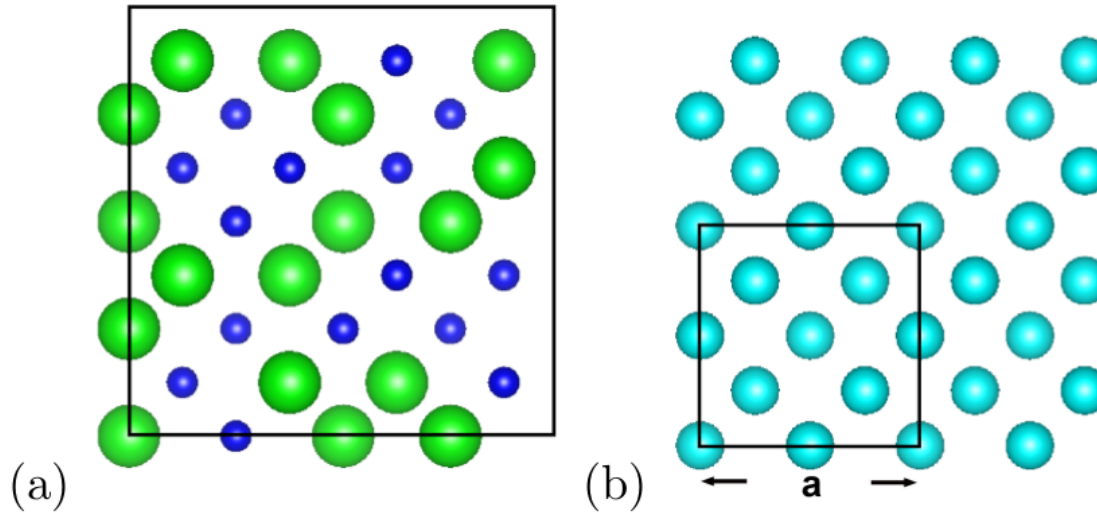


Virtual Crystal Approximation

$$k_{ph,\mathbf{n}} = \sum_{\boldsymbol{\kappa}} \sum_{\nu} \frac{k_B}{V} D_{ph,\mathbf{n}}\left(\frac{\boldsymbol{\kappa}}{\nu}\right)$$

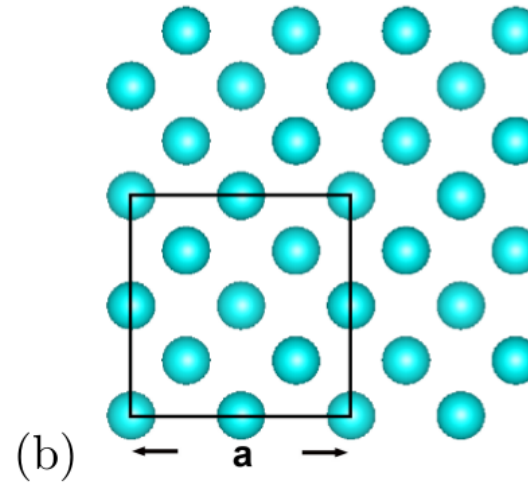
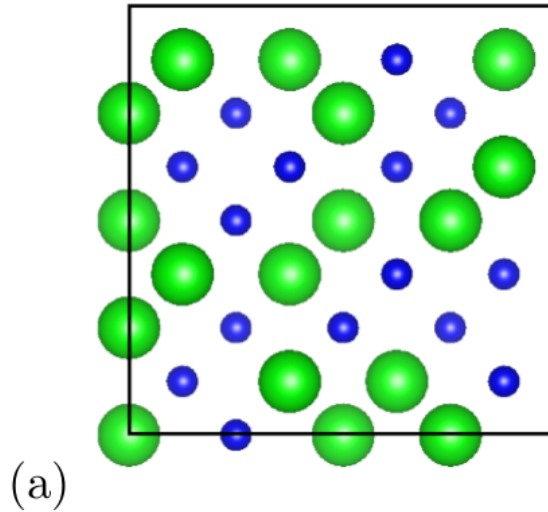
$$D_{ph,\mathbf{n}}\left(\frac{\boldsymbol{\kappa}}{\nu}\right) = v_{g,\mathbf{n}}^2\left(\frac{\boldsymbol{\kappa}}{\nu}\right) \tau\left(\frac{\boldsymbol{\kappa}}{\nu}\right)$$

Virtual Crystal Approximation



$$g_n = \sum_{\mu} c^\mu (1 - m^\mu / \bar{m}^\mu)^n$$

Virtual Crystal Approximation



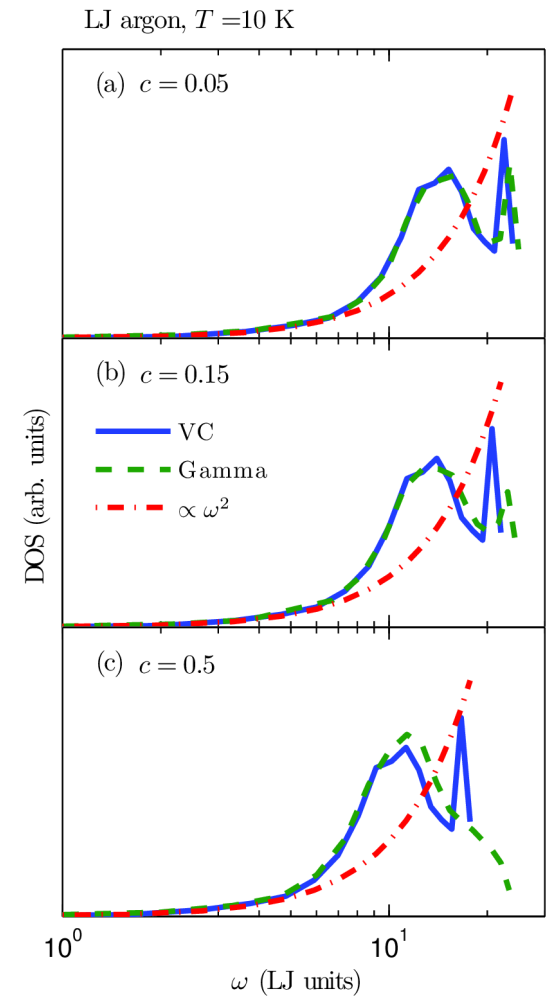
$$\tau_{p-d}(\kappa) \sim 1/\omega^4$$

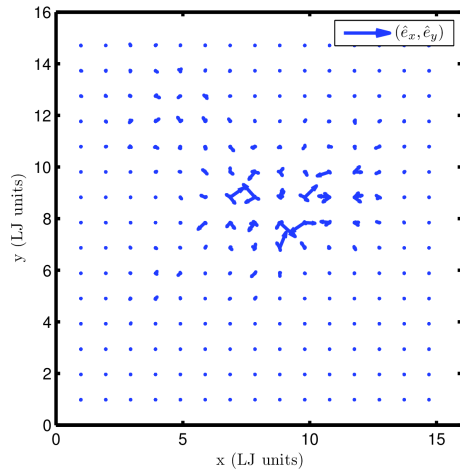
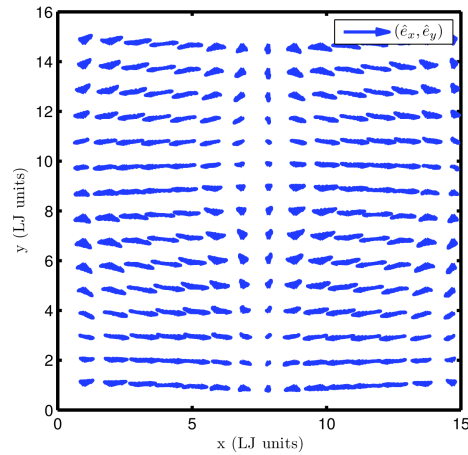
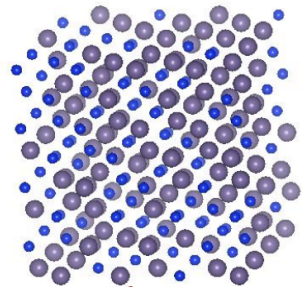
$$\tau_{p-p} \sim 1/\omega^2$$

Matthiessen's Rule

$$\frac{1}{\tau(\kappa)} = \frac{1}{\tau_{p-p}(\kappa)} + \frac{1}{\tau_{p-d}(\kappa)}$$

$$1/[(1-c)m^i + cm^j]^{1/2}$$

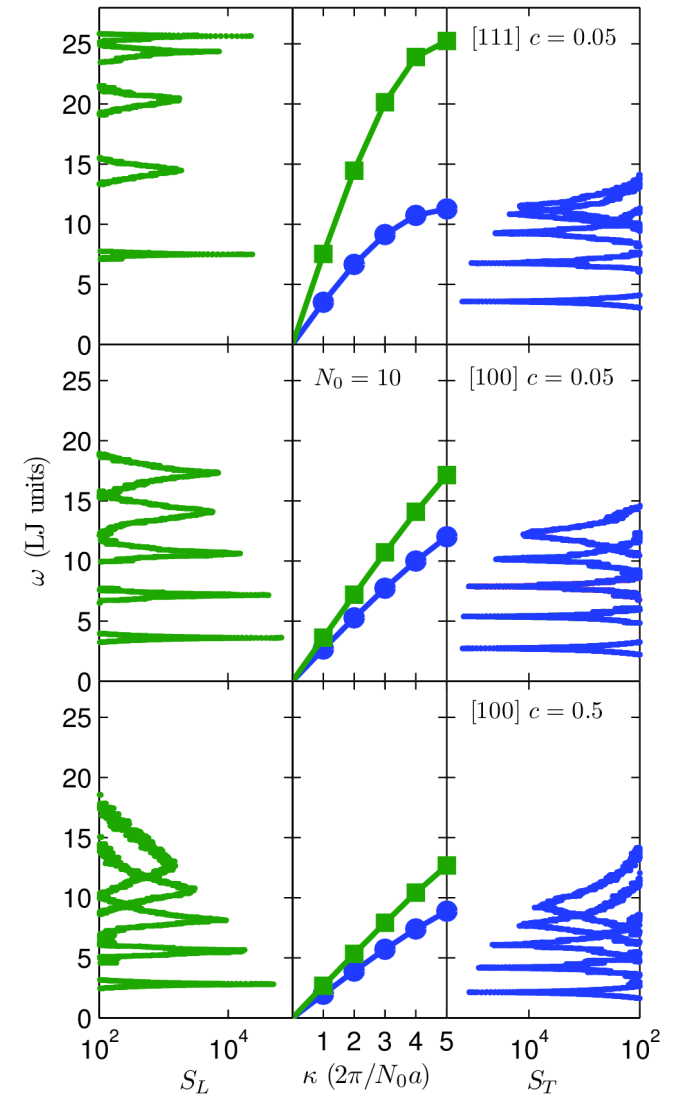
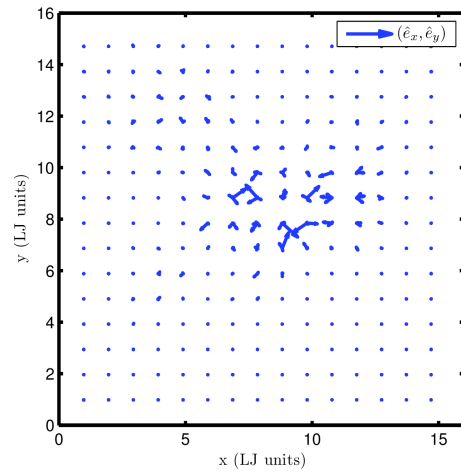
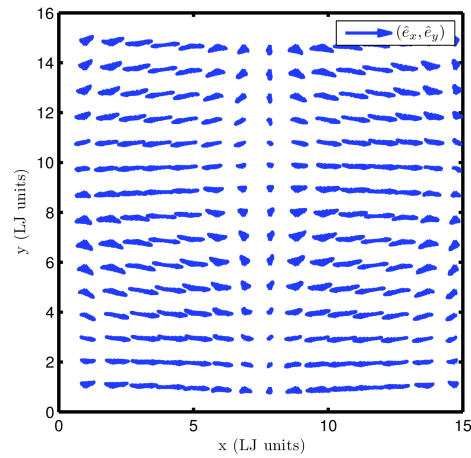
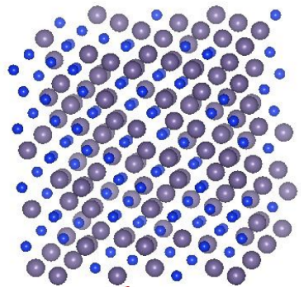


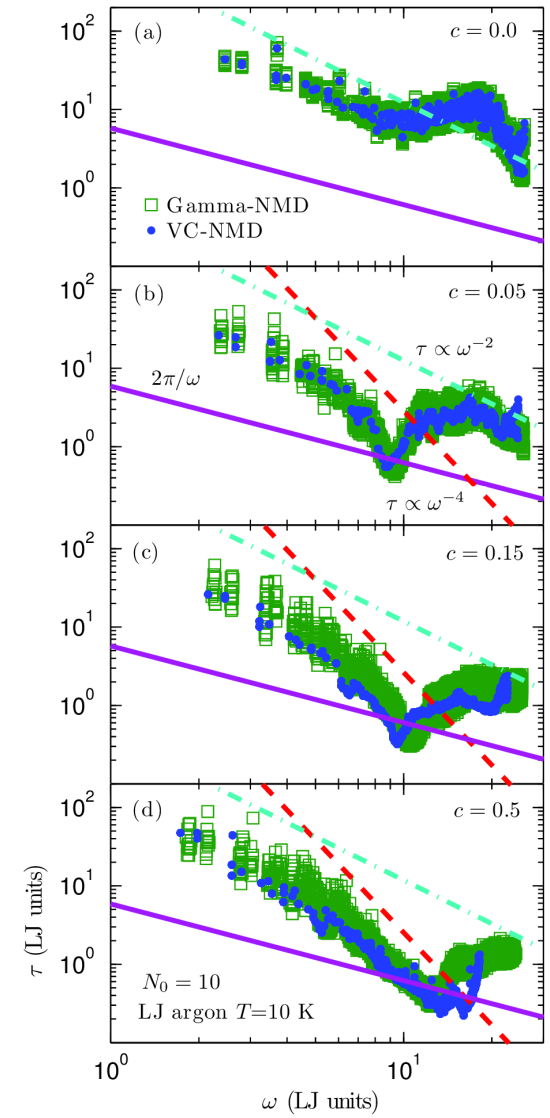


$$S^{L,T}(\kappa_{\nu}^C) = \sum_{\nu} E^{L,T}(\kappa_{\nu}^C) \delta(\omega - \omega(\kappa_{\nu}^C))$$

$$E^L(\kappa_{\nu}^C) = \left| \sum_b \hat{\kappa}_{\nu}^C \cdot e(\kappa_{\nu}^C) \exp[i\kappa_{\nu}^C \cdot \mathbf{r}_0^{(l=0)}] \right|^2$$

$$E^T(\kappa_{\nu}^C) = \left| \sum_b \hat{\kappa}_{\nu}^C \times e(\kappa_{\nu}^C) \exp[i\kappa_{\nu}^C \cdot \mathbf{r}_0^{(l=0)}] \right|^2$$





Virtual Crystal Approximation

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Diamond

GaN

si

Si,HS

Si/Ge

PbTe,PbTe/Se,
(1/4) $T_{\text{melt}} = 300\text{K}$

LJ,20K,
(1/4) T_{melt}



$$v_{g,\mathbf{n}}(\boldsymbol{\kappa}_{\nu}) = \frac{\partial \omega(\boldsymbol{\kappa}_{\nu})}{\partial \kappa}$$

$$q(\underset{\nu}{\boldsymbol{\kappa}}; t) = \sum_{\alpha, b, l}^{3, n, N} \sqrt{\frac{m_b}{N}} u_{\alpha}(\underset{b}{l}; t) e^*(\underset{\nu}{\boldsymbol{\kappa}} \underset{\alpha}{b}) \exp[i\boldsymbol{\kappa} \cdot \mathbf{r}_0(\underset{0}{l})]$$

$$E(\underset{\nu}{\boldsymbol{\kappa}}; t) = \frac{\omega(\underset{\nu}{\boldsymbol{\kappa}})^2}{\mathfrak{N}} q(\underset{\nu}{\boldsymbol{\kappa}}; t)^* q(\underset{\nu}{\boldsymbol{\kappa}}; t) + \frac{1}{\mathfrak{N}} \dot{q}(\underset{\nu}{\boldsymbol{\kappa}}; t)^* \dot{q}(\underset{\nu}{\boldsymbol{\kappa}}; t)$$

$$\tau(\underset{\nu}{\boldsymbol{\kappa}}) = \int_0^{t^*} \frac{< E(\underset{\nu}{\boldsymbol{\kappa}}; t) E(\underset{\nu}{\boldsymbol{\kappa}}; 0) >}{< E(\underset{\nu}{\boldsymbol{\kappa}}; 0) E(\underset{\nu}{\boldsymbol{\kappa}}; 0) >} dt$$

$$\tau = \frac{2\pi}{\omega}$$

$$\frac{1}{\tau_{p-d}(\boldsymbol{\kappa}_{\nu})} = \frac{\pi}{2} g_2 \omega^2(\boldsymbol{\kappa}_{\nu}) \text{DOS}(\omega(\boldsymbol{\kappa}_{\nu}))$$



modeling thermoelectric materials

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- anharmonic lattice dynamics + phonon defect lifetime (ald+taud).

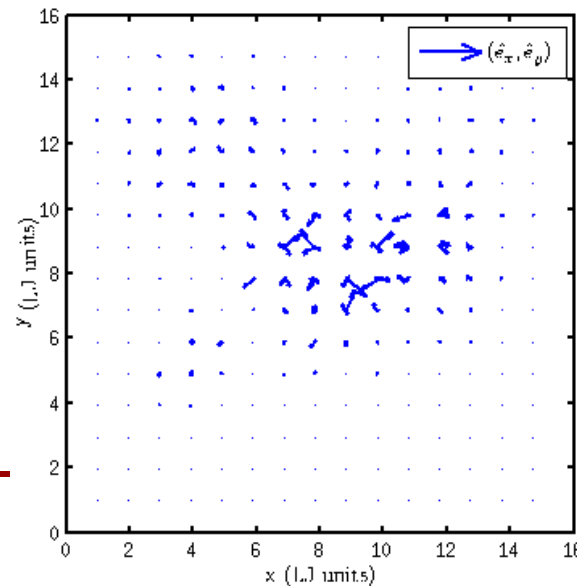
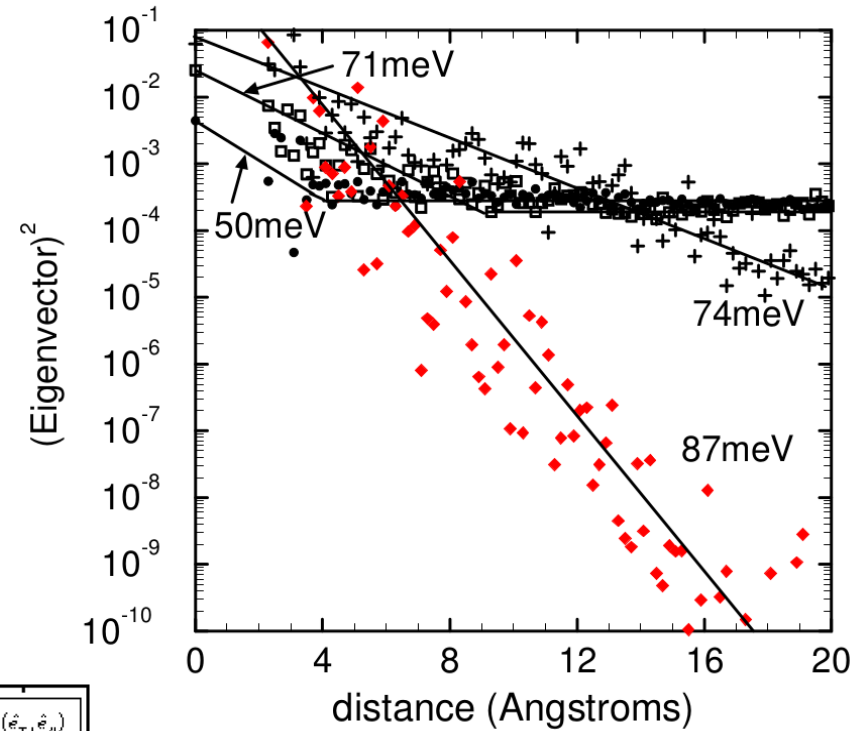
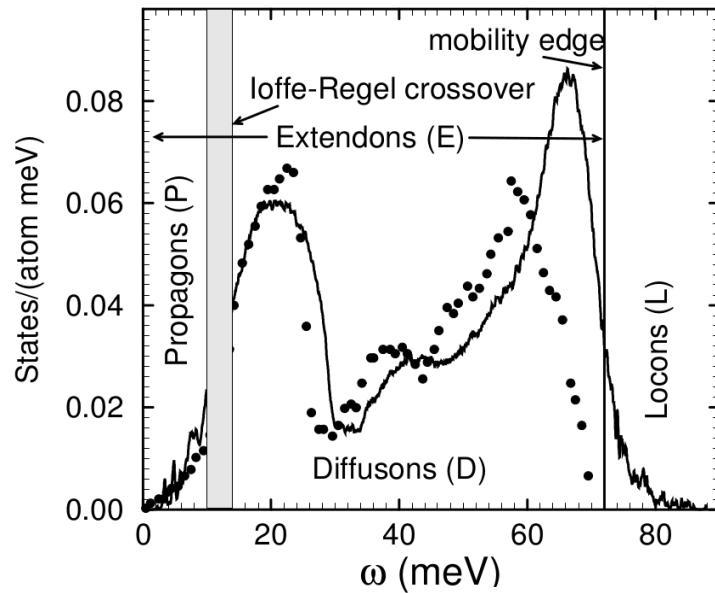
PRL 106, 045901 (2011)

- this approach referred to as **virtual crystal (vc)** approximation.
- ald+taud vc can be computationally cheap, even using ab initio.

is this approach valid?



propagons, diffusons, locons



Thermal Transport: Ordered and Disordered

$$k_{ph,n} = \sum_{\kappa} \sum_{\nu} \frac{k_B}{V} v_{g,n}^2(\kappa_{\nu}) \tau(\kappa_{\nu})$$

$$v_{g,n}(\kappa_{\nu}) = \partial \omega(\kappa_{\nu}) / \partial \kappa$$

$$D_{ph}(\kappa_{\nu}) = v_g^2(\kappa_{\nu}) \tau(\kappa_{\nu})$$

$$\Lambda(\kappa_{\nu}) = |v_g| \tau(\kappa_{\nu})$$

$$D_{ph}(\kappa_{\nu}) \approx 0 \longrightarrow$$

In a disordered material, it is not possible (in general) to specify v_g and τ independently

$$k_{AF} = \sum_{modes} \frac{k_B}{V} D_{AF}(\omega(\kappa_{\nu}^0))$$

Phys. Rev. B 59, 3551–3559 (1999)

http://prb.aps.org/abstract/PRB/v59/i5/p3551_1

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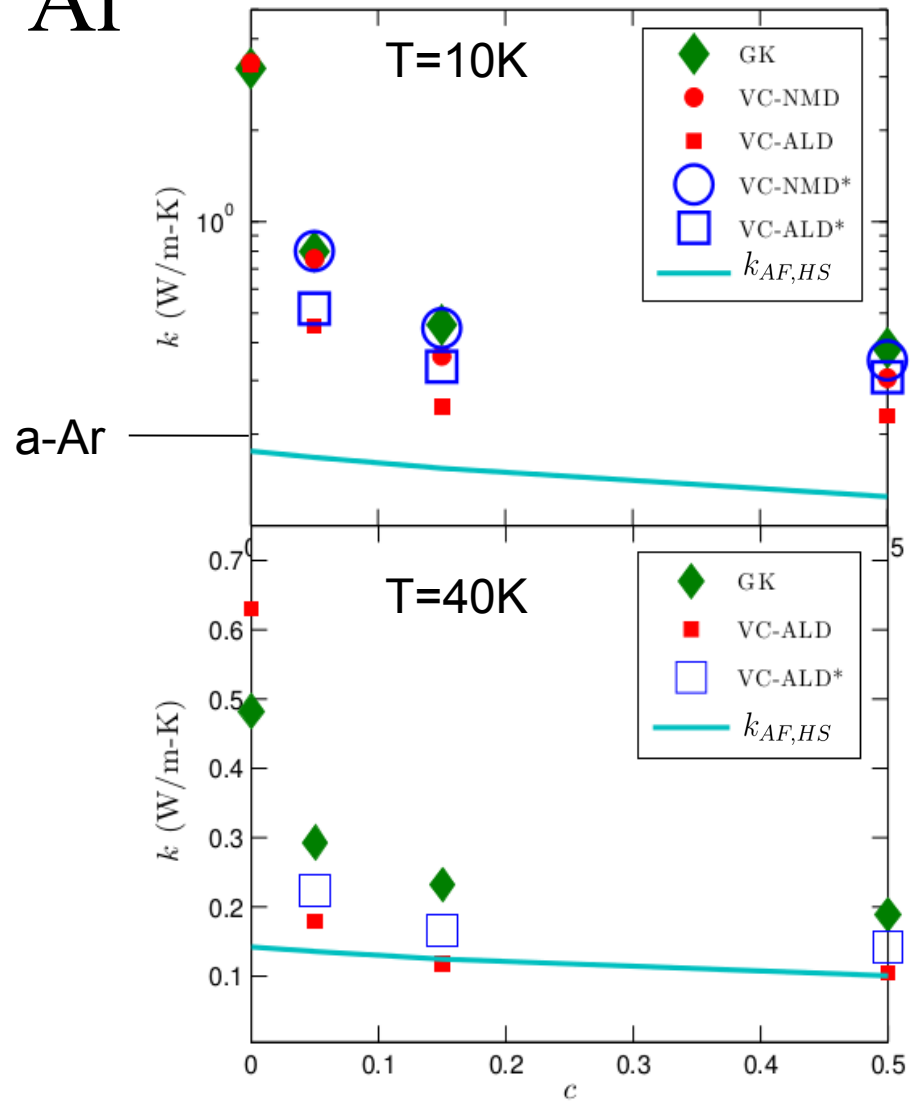
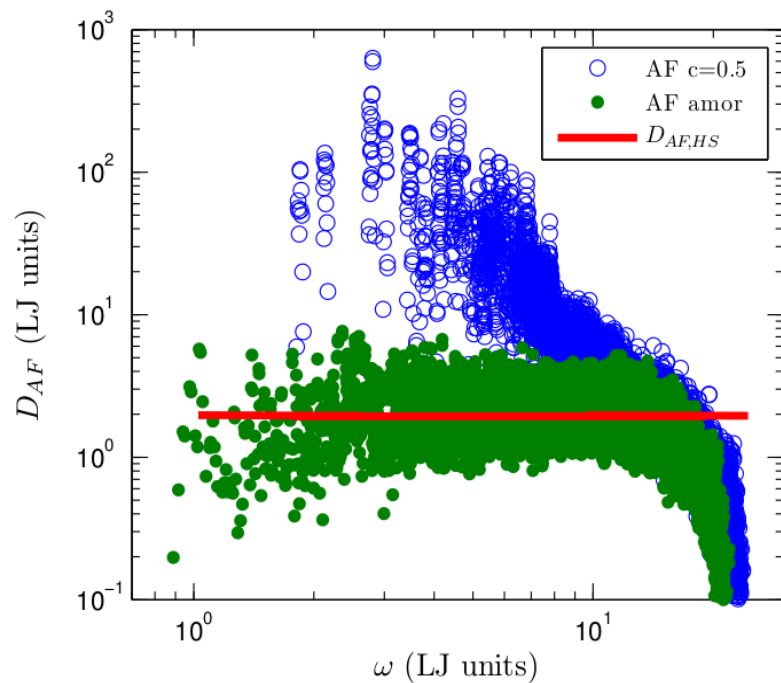
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http://prb.aps.org/abstract/PRB/v59/i5/p3551_1

High-Scatter Limit: LJ Ar

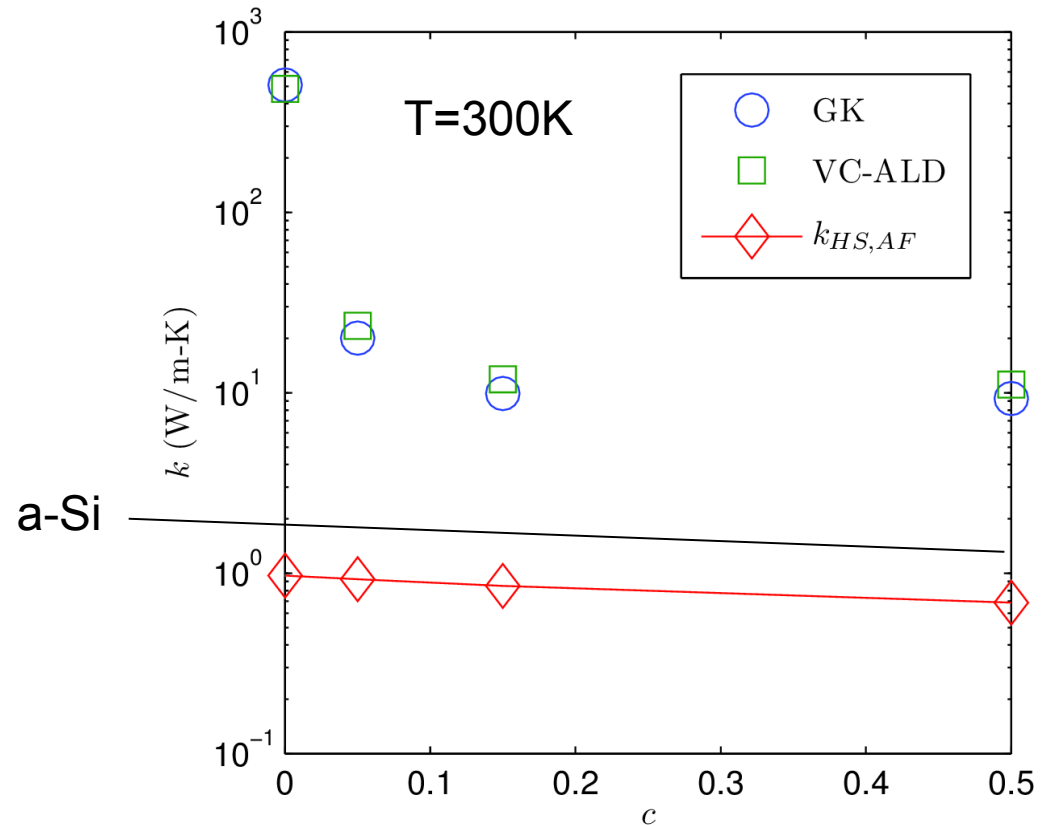
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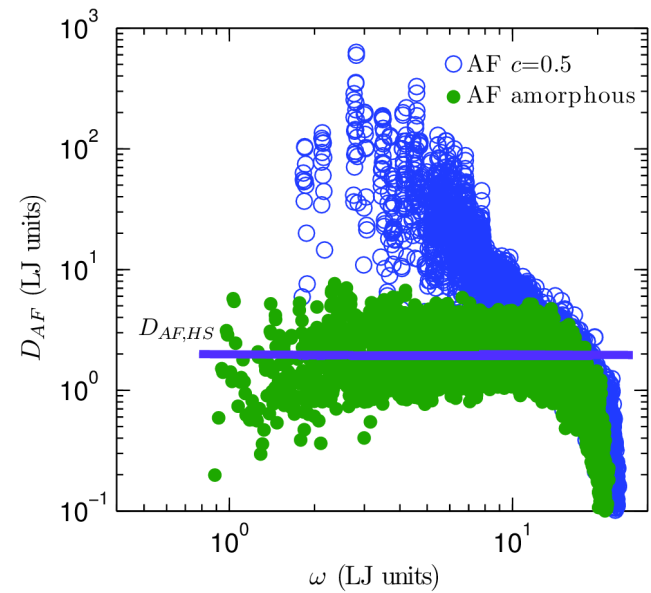
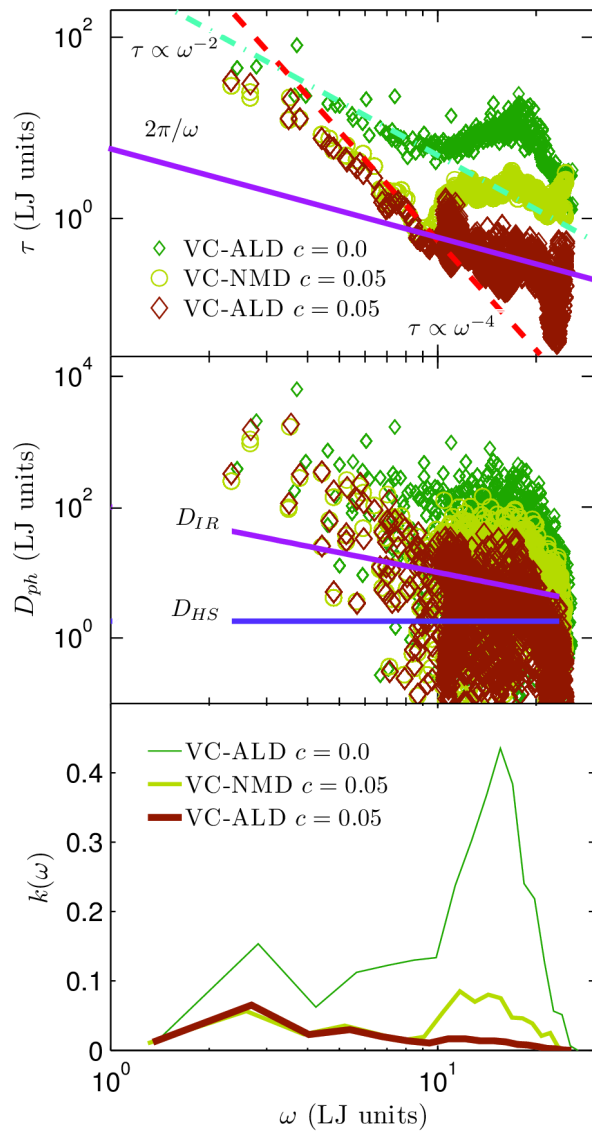
$$k_{AF,HS} = \frac{k_B}{V_b} b v_s a$$



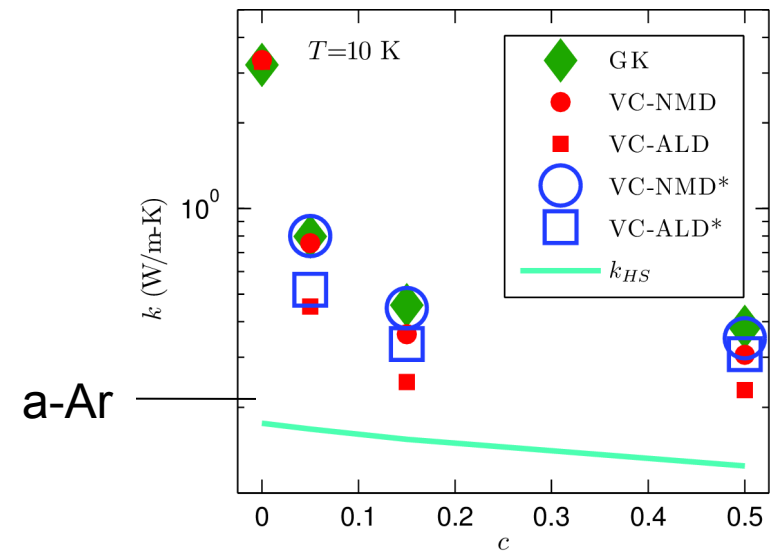
High-Scatter Limit: SW Si

$$k_{AF,HS} = \frac{k_B}{V_b} b v_s a$$

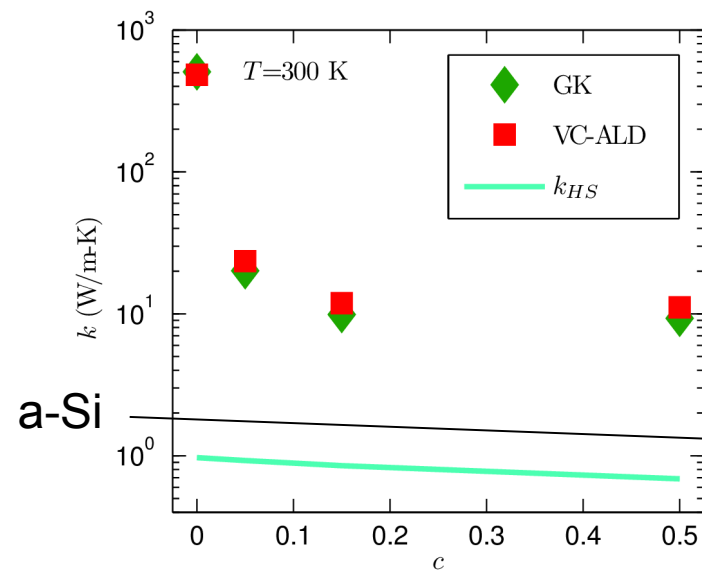
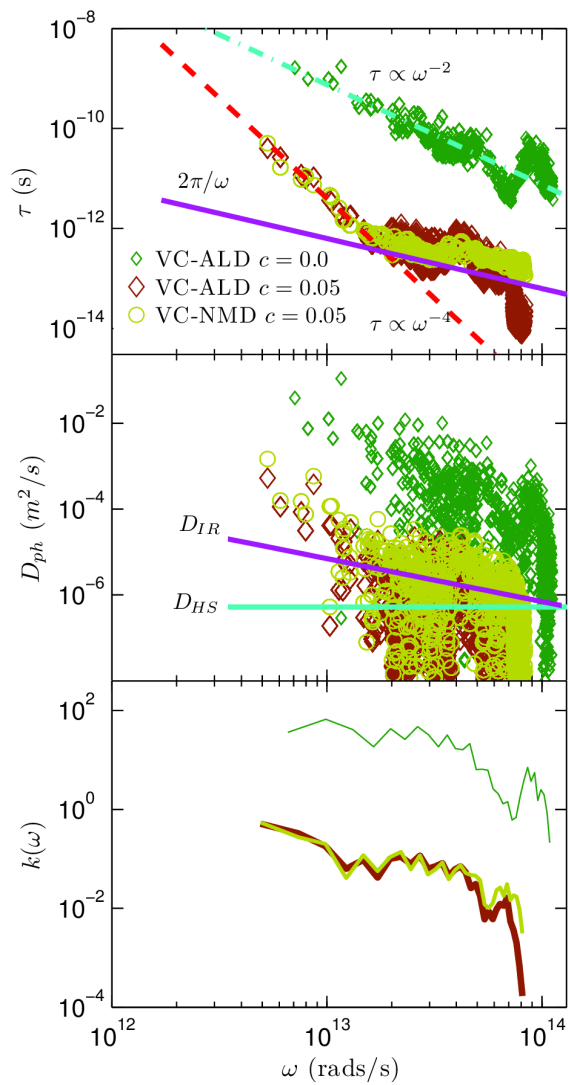


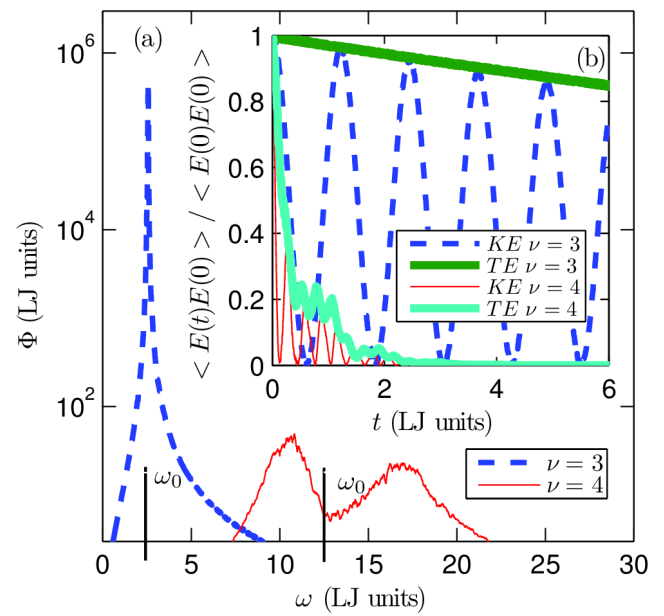


$$\frac{k(N_0)}{k_0} = 1 - \frac{c_0}{N_0}$$



a-Ar —



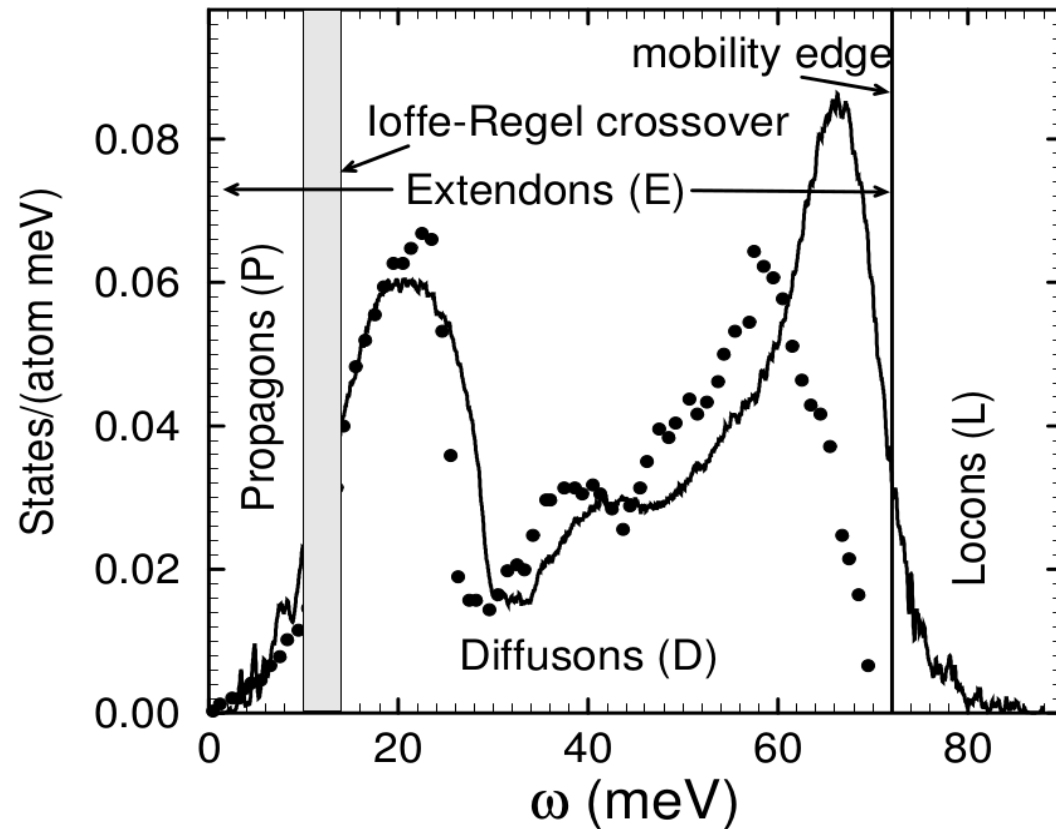


Propagons, Diffusons, Locons

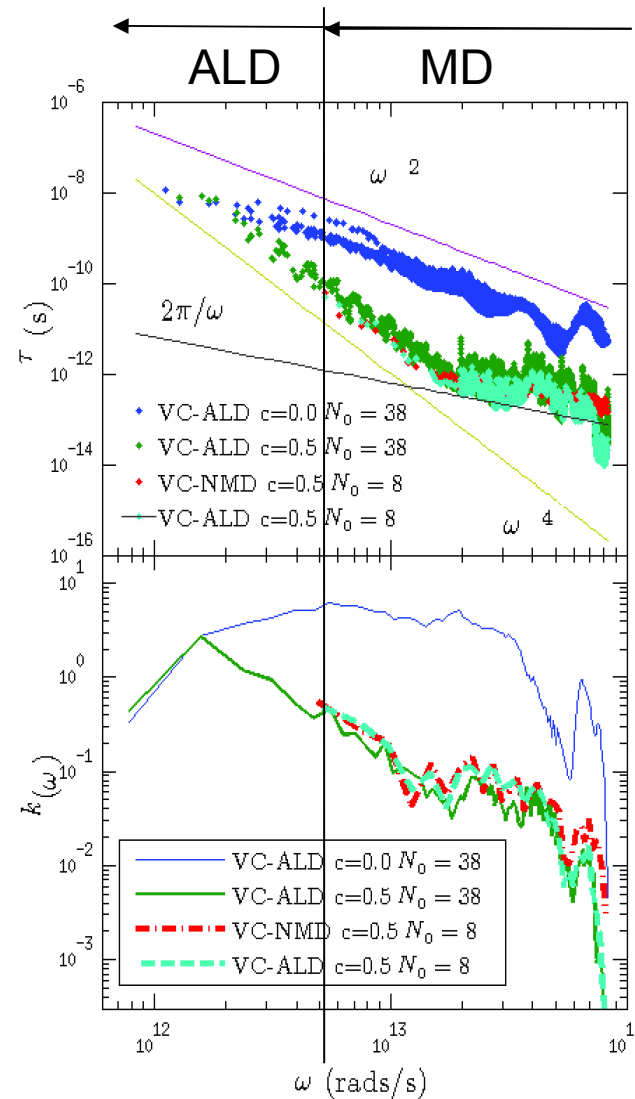
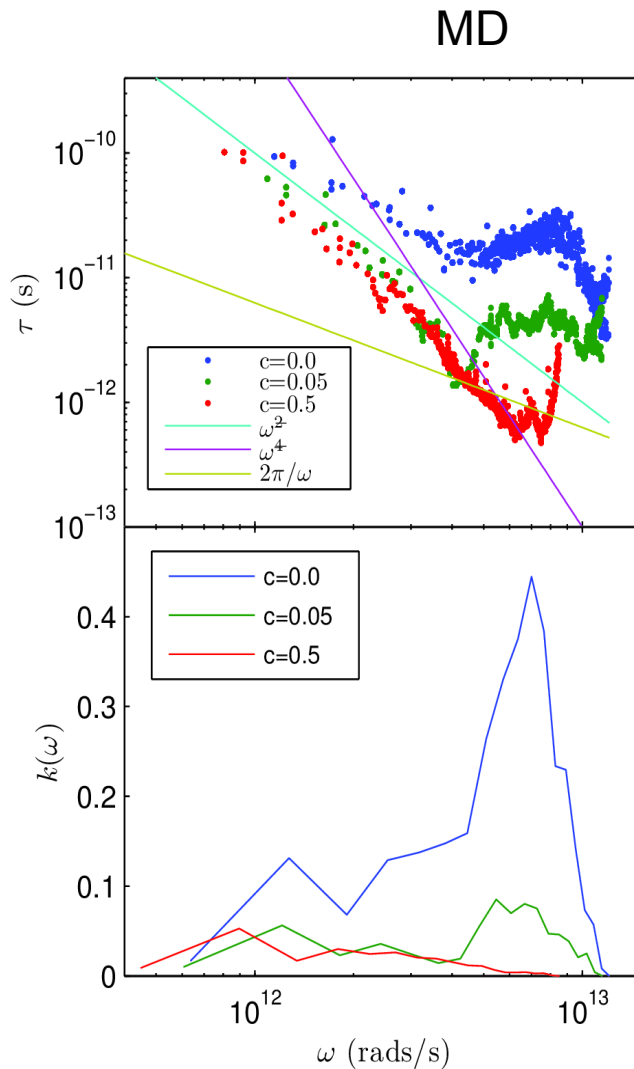
Numerical studies of amorphous silicon show that the lowest 4% of vibrational modes are plane-wave like (“propagons”) and the highest 3% of modes are localized (“locons”). The rest are neither plane-wave like nor localized. We call them “diffusons.”

\cite{diffusons_allen_1999}

vibrons $\left\{ \begin{array}{l} \text{extendons} \\ \text{locons} \end{array} \right\}$ $\left\{ \begin{array}{l} \text{propagons} \\ \text{diffusons} \end{array} \right\}$



Phonon Spectrum: LJ Ar vs SW Si



MD-based:

1E4 modes

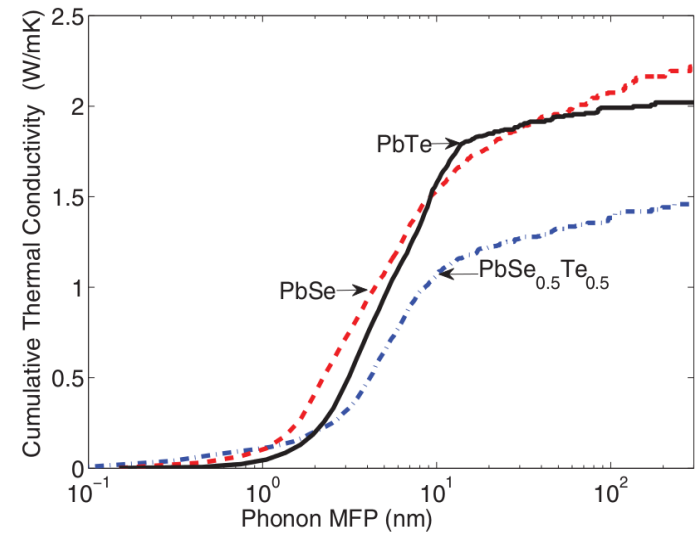
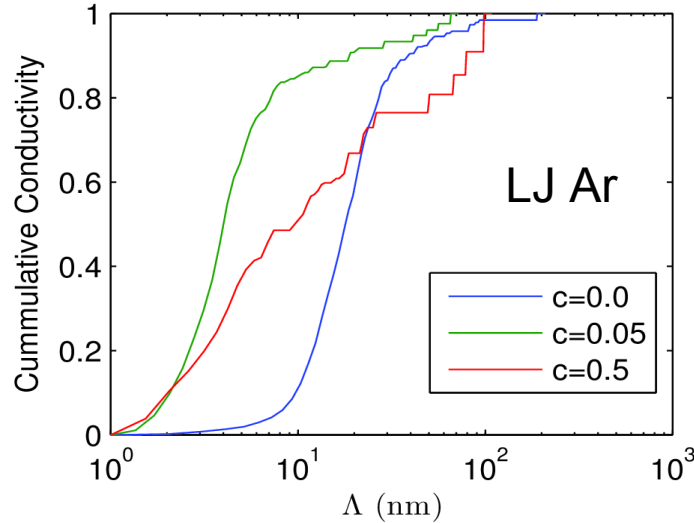
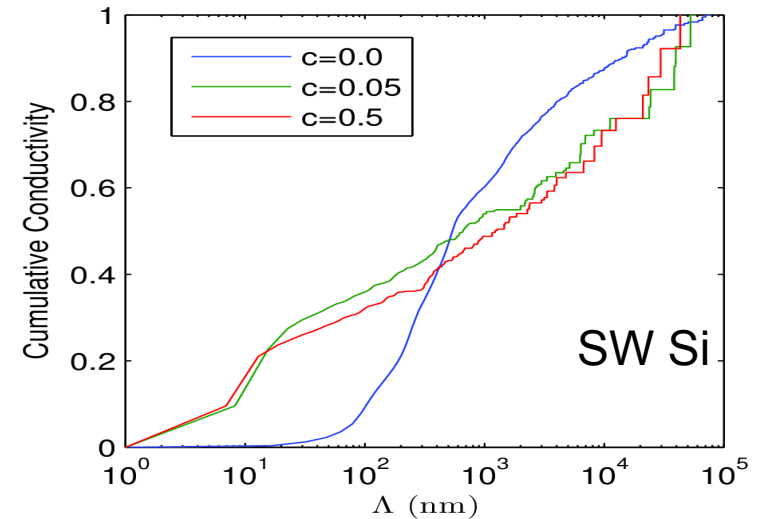
(7 days)*(100 cpu)

ALD:

1E6 modes

(7 days)*(12 cpu)

Conductivity Accumulation



PHYSICAL REVIEW B 85, 184303 (2012)

Diffuson Theory

- Allen Feldman theory of diffusons [1]:

$$k_{AF} = \sum_i C(\omega_i) D_{AF}(\omega_i)$$

$$D_{AF}(\omega_i) = \frac{\pi V^2}{3\hbar^2 \omega_i^2} \sum_{j \neq i} |S_{ij}|^2 \delta(\omega_i - \omega_j)$$

- Conservation of energy:

$$\delta(\omega_i - \omega_j)$$

- Heat current operator:

$$|S_{ij}|^2$$

- Ingredients: **harmonic** Lattice Dynamics

[1] Philip B. Allen and Joseph L. Feldman. Thermal conductivity of disordered harmonic solids. Physical Review B, 48(17):12581–12588, Nov 1993.